TAIWAN SEMICONDUCTOR

The Smartest Choice

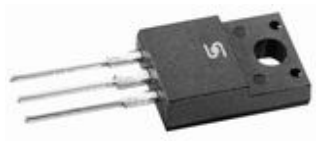
SFF1001G - SFF1008G

10.0AMPS Isolated Glass Passivated Super Fast Rectifier

ITO-220AB

Features

- ✧ UL Recognized File # E-326243
- ✧ High efficiency, low VF
- ✧ High current capability
- ✧ High reliability
- ✧ High surge current capability
- ✧ Low power loss
- ✧ For use in low voltage, high frequency inverter, Free wheeling, and polarity protection application
- ✧ Green compound with suffix "G" on packing code & prefix "G" on datecode



AEC-Q101 Qualified

Pb-Free

RoHS COMPLIANT

Mechanical Data

- ✧ Case: ITO-220AB Molded plastic
- ✧ Epoxy: UL 94V-0 rate flame retardant
- ✧ Terminals: Pure tin plated, lead free, solderable per MIL-STD-202, Method 208 guaranteed
- ✧ Polarity: As marked
- ✧ High temperature soldering: 260℃/10 seconds/.16",(4.06mm) from case
- ✧ Weight: 1.71 grams
- ✧ Mounting torque: 5 in - lbs. max.

Ordering Information (example)

Part No.	Package	Packing	Packing code	Packing code (Green)
SFF1001G	ITO-220AB	50 / TUBE	C0	C0G

Maximum Ratings and Electrical Characteristics

Rating at 25 ℃ ambient temperature unless otherwise specified.

Parameter	Symbol	SFF 1001G	SFF 1002G	SFF 1003G	SFF 1004G	SFF 1005G	SFF 1006G	SFF 1007G	SFF 1008G	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	150	200	300	400	500	600	V
Maximum RMS Voltage	V_{RMS}	35	70	105	140	210	280	350	420	V
Maximum DC Blocking Voltage	V_{DC}	50	100	150	200	300	400	500	600	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	10								A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	125								A
Maximum Instantaneous Forward Voltage (Note 1) @ 5A	V_F	0.975				1.3		1.7		V
Maximum Reverse Current @ Rated VR T_A=25 ℃ T_A=100 ℃	I_R	10 400								uA
Maximum Reverse Recovery Time (Note 2)	Trr	35								nS
Typical Junction Capacitance (Note 3)	Cj	70				50				pF
Typical Thermal Resistance	$R_{\theta jC}$	2								^{O}C/W
Operating Temperature Range	T_J	- 65 to + 150								^{O}C
Storage Temperature Range	T_{STG}	- 65 to + 150								^{O}C

Note 1: Pulse Test with PW=300 usec, 1% Duty Cycle

Note 2: Reverse Recovery Test Conditions: I_F=0.5A, I_R=1.0A, I_{RR}=0.25A

Note 3: Measured at 1 MHz and Applied Reverse Voltage of 4.0V D.C.

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RATINGS AND CHARACTERISTIC CURVES (SFF1001G THRU SFF1008G)

FIG.1 FORWARD CURRENT DERATING CURVE

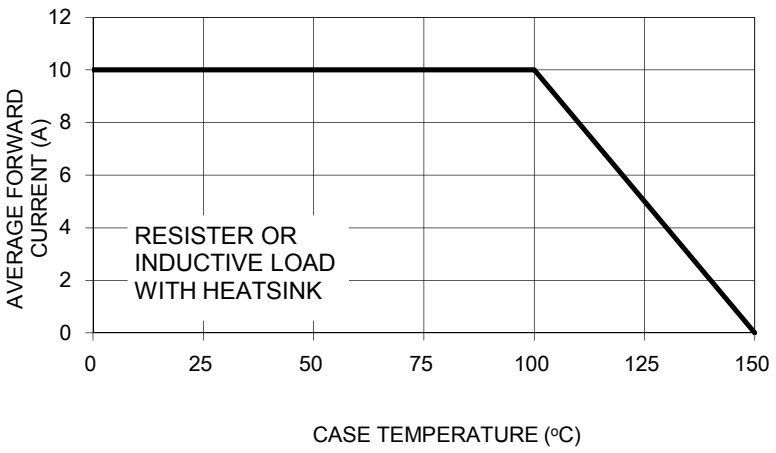


FIG. 2 TYPICAL REVERSE CHARACTERISTICS

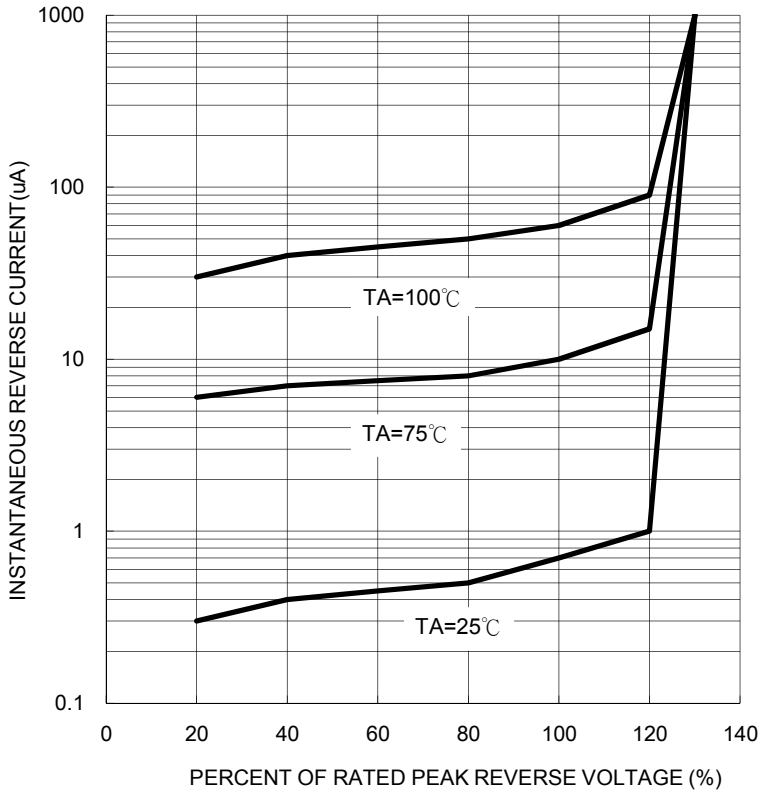


FIG. 3 MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

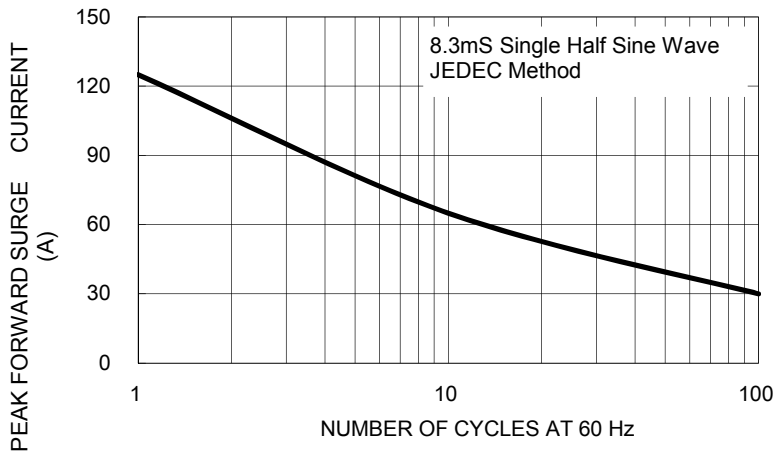


FIG. 5 TYPICAL FORWARD CHARACTERISTICS

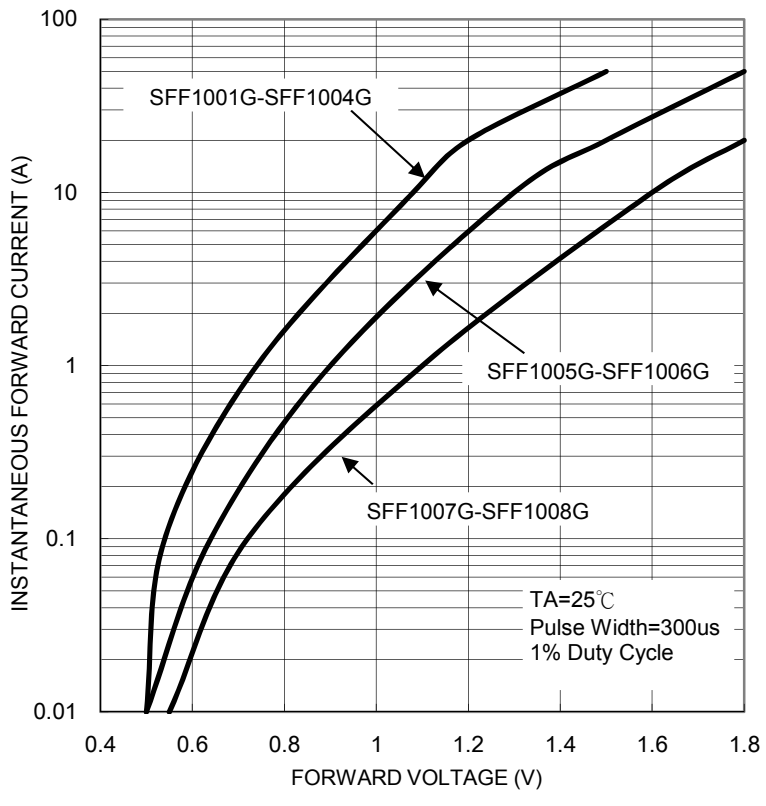


FIG. 4 TYPICAL JUNCTION CAPACITANCE

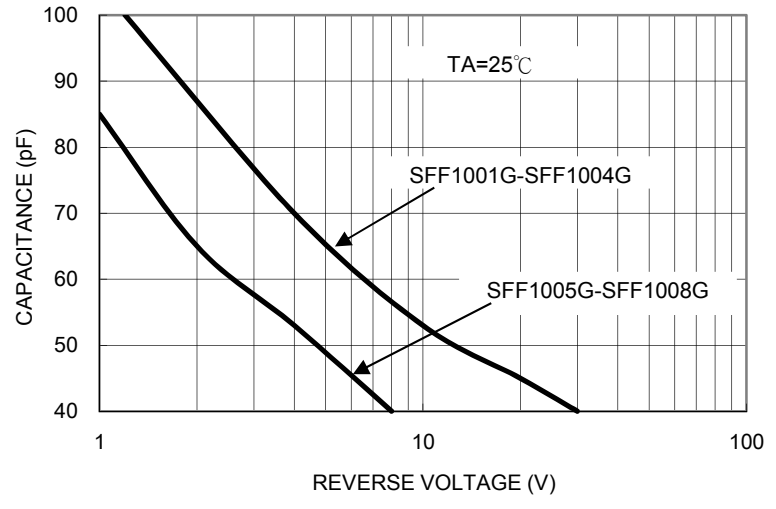
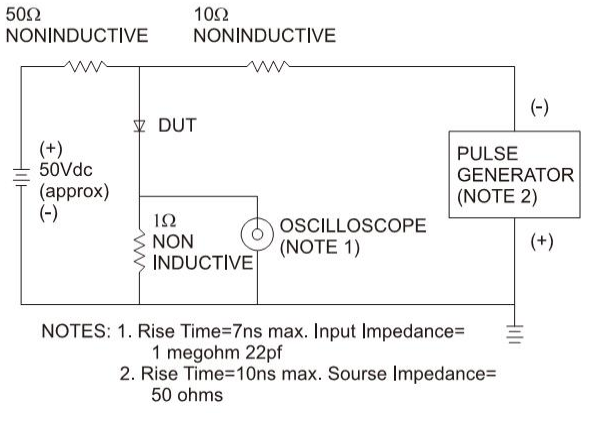
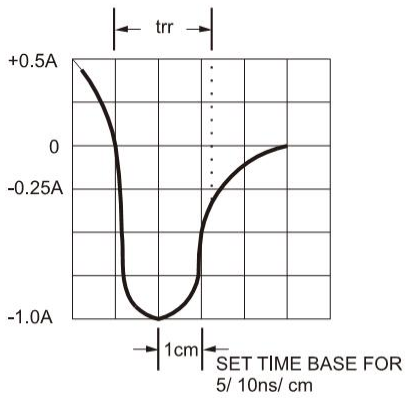


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM





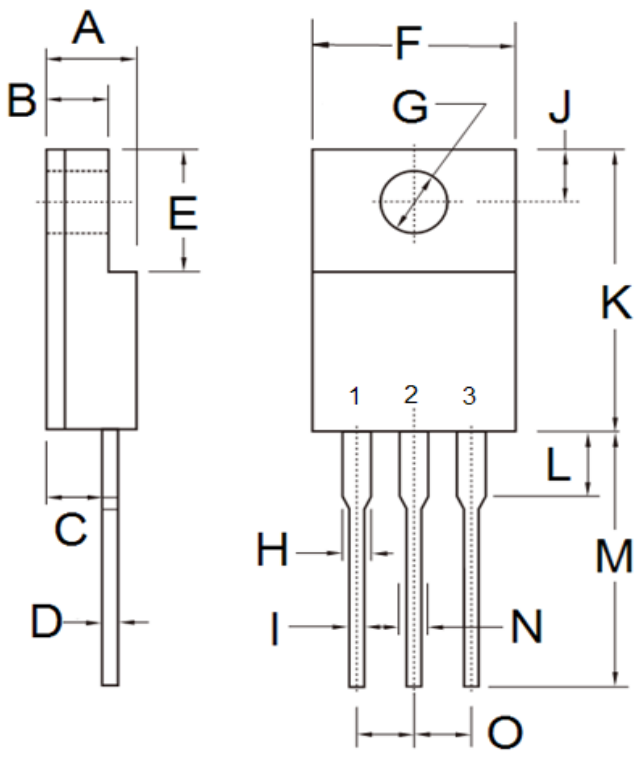
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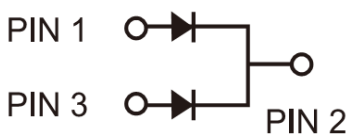
Ordering information

Part No.	Package	BULK Packing	Packing code	Packing code (Green)
SFF100xG	ITO-220AB	50 / TUBE	C0	C0G

Note: "x" is Device Code from "1" thru "8".

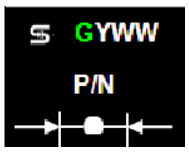
Dimensions





DIM.	Unit(mm)		Unit(inch)	
	Min	Max	Min	Max
A	4.30	4.70	0.169	0.185
B	2.50	3.16	0.098	0.124
C	2.30	2.96	0.091	0.117
D	0.46	0.76	0.018	0.030
E	6.30	6.90	0.248	0.272
F	9.60	10.30	0.378	0.406
G	3.00	3.40	0.118	0.134
H	0.95	1.45	0.037	0.057
I	0.50	0.90	0.020	0.035
J	2.40	3.20	0.094	0.126
K	14.80	15.50	0.583	0.610
L	-	4.10	-	0.161
M	12.60	13.80	0.496	0.543
N	-	1.80	-	0.071
O	2.41	2.67	0.095	0.105

Marking Diagram



P/N = Specific Device Code
G = Green Compound
YWW = Date Code